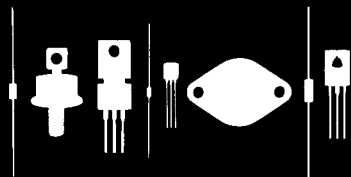


Central  
Semiconductor Corp.  
Central  
Semiconductor Corp.  
Central  
Semiconductor Corp.  
**Central™  
Semiconductor Corp.**

145 Adams Avenue  
Hauppauge, New York 11788



1N662,A  
1N663,A  
SILICON SWITCHING DIODE

JEDEC DO-35 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 1N662 Series types are high speed Silicon Switching Diodes designed for general purpose applications.

MAXIMUM RATINGS ( $T_A=25^\circ\text{C}$  unless otherwise noted)

	SYMBOL		UNIT
Peak Working Reverse Voltage	$V_{RWM}$	80	V
Average Forward Current	$I_O$	150	mA
Forward Steady State Current	$I_F$	200	mA
Peak Forward Surge Current	$I_{FSM}$	4.0	A
Power Dissipation	$P_D$	500	mW
Operating and Storage Junction Temperature	$T_J, T_{stg}$	-65 TO +200	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ( $T_A=25^\circ\text{C}$  unless otherwise noted)

SYMBOL		1N662		1N662A		1N663		1N663A		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
$I_R$	$V_R=10V$		1.0		1.0		-		-	$\mu\text{A}$
$I_R$	$V_R=10V, T_A=100^\circ\text{C}$		20		20		-		-	$\mu\text{A}$
$I_R$	$V_R=50V$		20		20		-		-	$\mu\text{A}$
$I_R$	$V_R=50V, T_A=100^\circ\text{C}$		100		100		-		-	$\mu\text{A}$
$I_R$	$V_R=75V$		-		-		5.0		1.0	$\mu\text{A}$
$I_R$	$V_R=75V, T_A=100^\circ\text{C}$		-		-		50		15	$\mu\text{A}$
$BV_R$	$I_R=100\mu\text{A}$	100		100		100		100		V
$V_F$	$I_F=10\text{mA}$		1.0		-		-		-	V
$V_F$	$I_F=100\text{mA}$		-		1.0		1.0		1.0	V
$t_{rr}$	(See Note #1)		500		-		-		-	ns
$t_{rr}$	(See Note #1)		-		300		-		-	ns
$t_{rr}$	(See Note #2)		-		-		500		-	ns
$t_{rr}$	(See Note #2)		-		-		-		300	ns

Notes:

1. Test Conditions:  $V_R=40V, I_f=5.0\text{mA}, R_L=2.3\text{k}\Omega, C_L=40\text{pF}, \text{Recov. to } 100\text{k}\Omega$
2. Test Conditions:  $V_R=40V, I_f=5.0\text{mA}, R_L=2.3\text{k}\Omega, C_L=40\text{pF}, \text{Recov. to } 200\text{k}\Omega$

**Central™  
Semiconductor Corp.**

145 Adams Avenue  
Hauppauge, NY 11788 USA  
Tel: (631) 435-1110 • Fax: (631) 435-1824  
www.centrasemi.com